



# HDP-CVD Series

## Uni-body Design Concept

Foot-print outstanding (ref 1.0m\*1.5m)

## Process Design Kits

Better process performance

## Temperature Control

Chamber liner, electrode temperature control suitable for different process application

## Step Coverage

Excellent step covering capability, tuned as a parameter dependently

## Cost or Performance Orientation

RF, Pump, Values etc. depending on requirements

## Sample Handling Options

Open-Load or Load-Lock



Specification	Parameters
Wafer Size Range	4,6,8,12 inch or multi-wafers optional
Deposition Materials	Si/SiO <sub>2</sub> /SiN <sub>x</sub> /SiON/SiC, etc
Vacuum	TMP&Mechanical Pump
RF Power	Full Range: Source 1000-3000W, Bias 300-1000W, optional
Gas System	6 lines(Standard) or customized
Wafer Stage Temperature Range	From 20°C to 200°C
Non-Uniformity	Less than ±5%(Edge Exclusion)